

# **HAT2200WP**

# Silicon N Channel Power MOS FET Power Switching

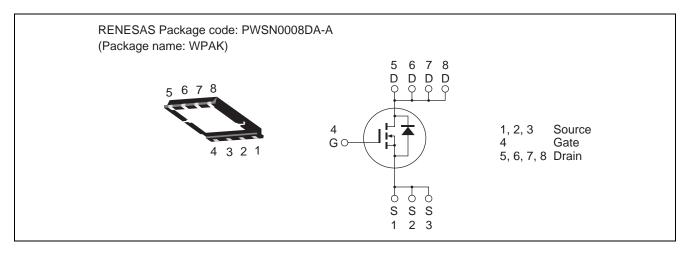
REJ03G1678-0310 Rev.3.10 May 13, 2010

#### **Features**

- Capable of 8 V gate drive
- Low drive current
- High density mounting
- Low on-resistance

 $R_{DS(on)} = 22 \text{ m}\Omega \text{ typ. (at } V_{GS} = 10 \text{ V})$ 

#### **Outline**



### **Absolute Maximum Ratings**

 $(Ta = 25^{\circ}C)$ 

Item	Symbol	Ratings	Unit
Drain to source voltage	V <sub>DSS</sub>	100	V
Gate to source voltage	$V_{GSS}$	±20	V
Drain current	I <sub>D</sub>	20	Α
Drain peak current	I <sub>D(pulse)</sub> Note1	80	Α
Body-drain diode reverse drain current	I <sub>DR</sub>	20	Α
Avalanche current	I <sub>AP</sub> Note 2	20	Α
Avalanche energy	E <sub>AR</sub> Note 2	40	mJ
Channel dissipation	Pch Note3	20	W
Channel to case thermal Impedance	θch-c Note3	6.25	°C/W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	−55 to +150	°C

Notes: 1. PW  $\leq$  10  $\mu$ s, duty cycle  $\leq$  1%

2. Value at Tch = 25°C, Rg  $\geq$  50  $\Omega$ 

3. Tc = 25°C

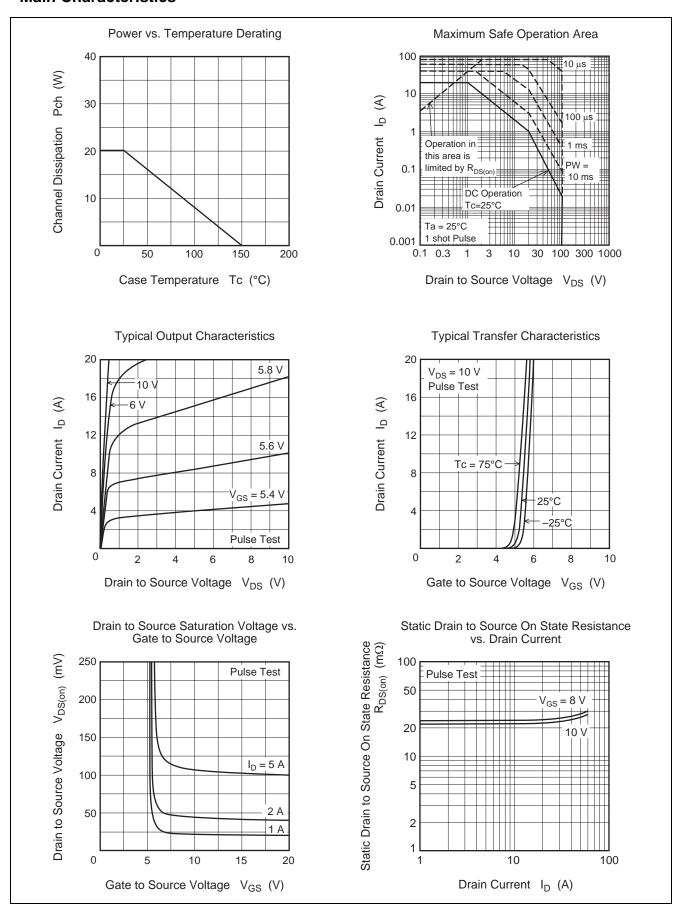
# **Electrical Characteristics**

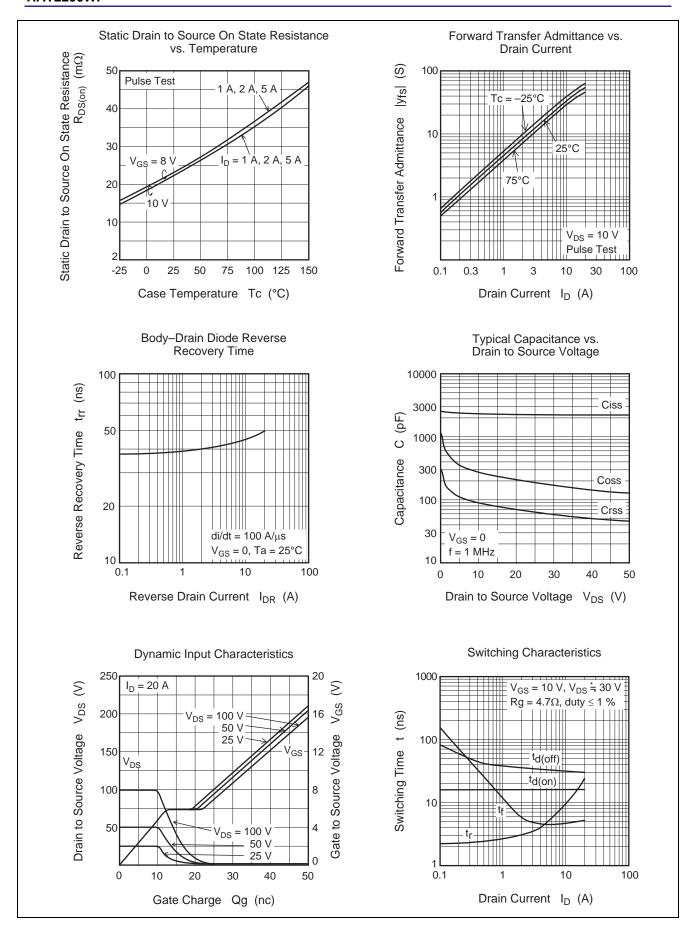
 $(Ta = 25^{\circ}C)$ 

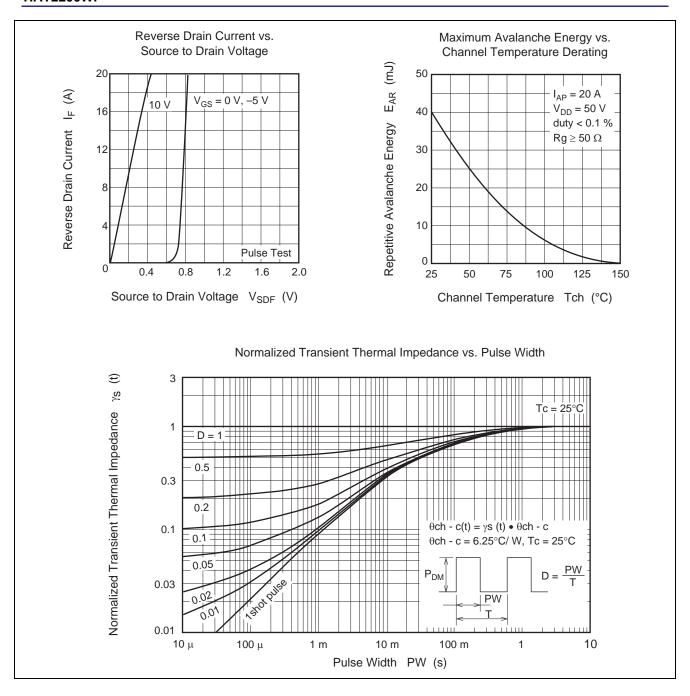
Item	Symbol	Min	Тур	Max	Unit	Test Conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	100	_	_	V	$I_D = 10 \text{ mA}, V_{GS} = 0$
Gate to source leak current	$I_{GSS}$	_	_	±0.1	μΑ	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0$
Zero gate voltage drain current	I <sub>DSS</sub>	_	_	1	μΑ	$V_{DS} = 100 \text{ V}, V_{GS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	3.5	_	5.0	V	$V_{DS} = 10 \text{ V}, I_{D} = 1 \text{ mA}$
Static drain to source on state	R <sub>DS(on)</sub>	_	22	28	mΩ	$I_D = 10 \text{ A}, V_{GS} = 10 \text{ V}^{Note4}$
resistance	R <sub>DS(on)</sub>	_	23	33	mΩ	$I_D = 10 \text{ A}, V_{GS} = 8 \text{ V}^{\text{Note4}}$
Forward transfer admittance	y <sub>fs</sub>	19	33	_	S	$I_D = 10 \text{ A}, V_{DS} = 10 \text{ V}^{Note4}$
Input capacitance	Ciss	_	2300	_	pF	V <sub>DS</sub> = 10 V
Output capacitance	Coss	_	280	_	pF	$V_{GS} = 0$
Reverse transfer capacitance	Crss	_	90	_	pF	f = 1 MHz
Gate resistance	Rg	_	1.3	_	Ω	
Total gate charge	Qg	_	32	_	nc	V <sub>DD</sub> = 50 V
Gate to source charge	Qgs	_	12	_	nc	V <sub>GS</sub> = 10 V
Gate to drain charge	Qgd	_	8	_	nc	I <sub>D</sub> = 20 A
Turn-on delay time	t <sub>d(on)</sub>	_	16	_	ns	$V_{GS} = 10 \text{ V}, I_{D} = 10 \text{ A}$
Rise time	t <sub>r</sub>	_	9.5	_	ns	$V_{DD} \cong 30 \text{ V}$
Turn-off delay time	t <sub>d(off)</sub>	_	31	_	ns	$R_L = 3 \Omega$
Fall time	t <sub>f</sub>	_	4.6	_	ns	$Rg = 4.7 \Omega$
Body-drain diode forward voltage	$V_{DF}$		0.82	1.07	V	$I_F = 20 \text{ A}, V_{GS} = 0^{\text{Note4}}$
Body-drain diode reverse recovery time	t <sub>rr</sub>	_	50	_	ns	$I_F = 20 \text{ A}, V_{GS} = 0$ $di_F/dt = 100 \text{ A}/ \mu \text{s}$

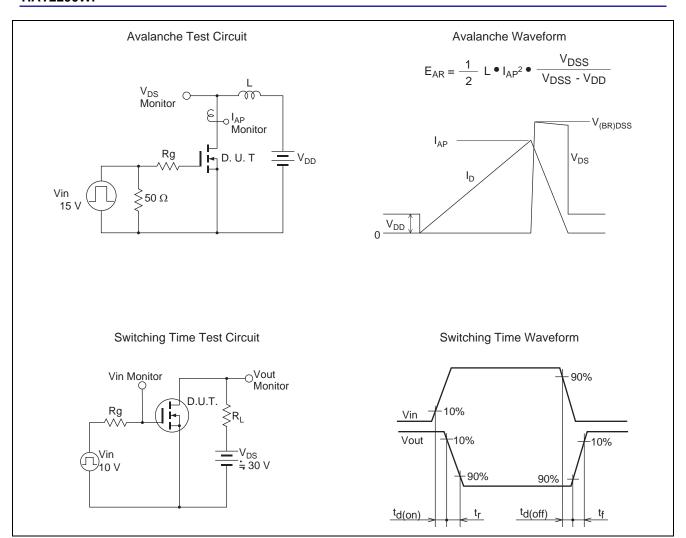
Notes: 4. Pulse test

#### **Main Characteristics**

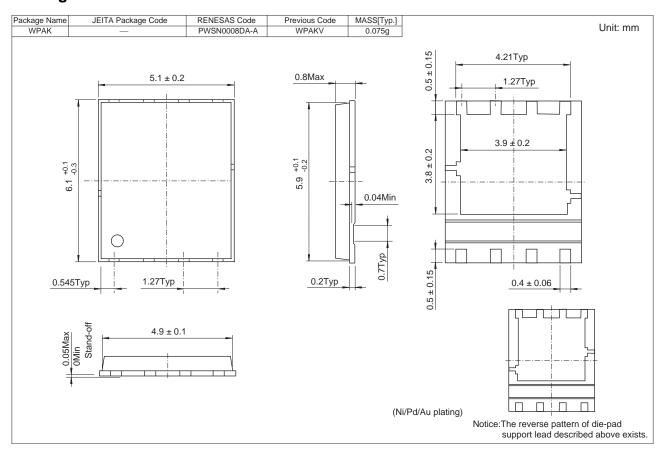








# **Package Dimensions**



# **Ordering Information**

Part No.	Quantity	Shipping Container
HAT2200WP-EL-E	2500 pcs	Taping

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